

What is Claimed is:

1. A method for forming a word line of a semiconductor device, comprising the steps of:
 - 5 (a) forming a sacrificial insulation film on a semiconductor substrate including a device isolation film defining an active region;
 - (b) selectively etching the sacrificial insulation film to form an I-type sacrificial insulation film pattern
 - 10 on a predetermined region of the active region where a channel region is to be formed;
 - (c) forming a source/drain region on the semiconductor substrate at both sides of the sacrificial insulation film pattern;
 - 15 (d) forming a first interlayer insulation film on the entire surface;
 - (e) planarizing the first interlayer insulation film to expose a top surface of the sacrificial insulation film pattern;
 - 20 (f) sequentially forming a insulation film and a second interlayer insulation film on the entire surface;
 - (g) etching the second interlayer insulation film and insulation film using a word line mask;
 - (h) removing the sacrificial insulation film pattern

to expose the semiconductor substrate;

(i) growing a gate oxide film on the exposed portion
of the semiconductor substrate;

(j) forming a conductive layer on the entire surface;

5 and

(k) planarizing the conductive layer to expose the
second interlayer insulation film.

2. The method according to claim 1, wherein the

10 step (h) is a dry etch back process, a wet etch back
process or a chemical mechanical polishing.

3. The method according to claim 1, wherein the

step (e) is a dry etch back process or a wet etch back
15 process.

4. The method according to claim 1, wherein the

step (e) is a chemical mechanical polishing.

20 5. The method according to claim 1, wherein the

step (k) is a dry etch back process or a wet etch back
process.

6. The method according to claim 1, wherein the

step (k) is a chemical mechanical polishing.